



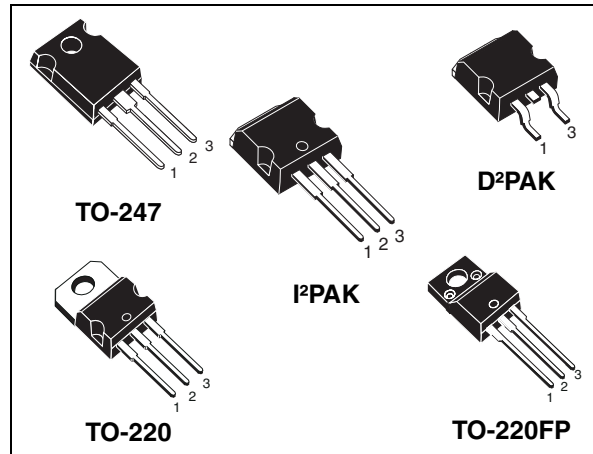
# STB18NM60N, STF18NM60N, STI18NM60N STP18NM60N, STW18NM60N

N-channel 600 V, 0.27  $\Omega$ , 13 A MDmesh™ II Power MOSFET  
in TO-220, TO-220FP, TO-247, D<sup>2</sup>PAK and I<sup>2</sup>PAK

## Features

Order codes	V <sub>DSS</sub> (@T <sub>jmax</sub> )	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>W</sub>
STB18NM60N	650 V	< 0.285 $\Omega$	13 A	110 W
STF18NM60N				30 W
STI18NM60N				110 W
STP18NM60N				
STW18NM60N				

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



## Application

Switching applications

## Description

These devices are made using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram

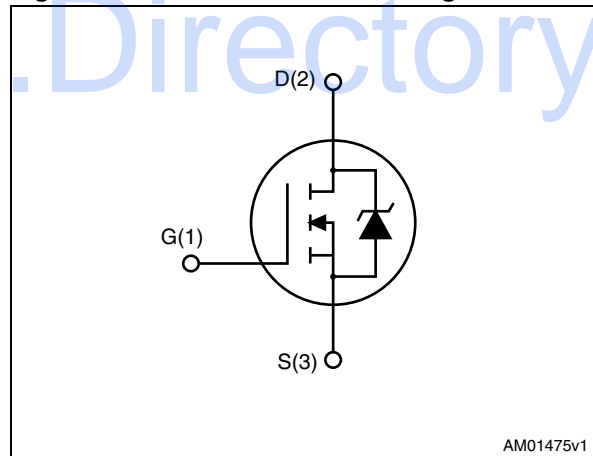


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB18NM60N	18NM60N	D <sup>2</sup> PAK	Tape and reel
STF18NM60N	18NM60N	TO-220FP	Tube
STI18NM60N	18NM60N	I <sup>2</sup> PAK	Tube
STP18NM60N	18NM60N	TO-220	Tube
STW18NM60N	18NM60N	TO-247	Tube

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		D <sup>2</sup> PAK,I <sup>2</sup> PAK TO-220,TO-247	TO-220FP	
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	600		V
V <sub>GS</sub>	Gate- source voltage	± 25		
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	13	13 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	8.2	8.2 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	52	52 <sup>(1)</sup>	A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	110	30	W
I <sub>AR</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by T <sub>J</sub> max)	4.5		A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>J</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	350		mJ
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	15		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T <sub>C</sub> =25 °C)		2500	V
T <sub>J</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	-55 to 150		°C

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- I<sub>SD</sub> ≤ 13 A, di/dt ≤ 400 A/μs, peak V<sub>DS</sub> ≤ V<sub>(BR)DSS</sub>

**Table 3. Thermal data**

Symbol	Parameter	D <sup>2</sup> PAK	I <sup>2</sup> PAK	TO-220	TO-247	TO-220FP	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max	1.14				4.17	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-amb max		62.5	50		62.5	°C/W
T <sub>l</sub>	Maximum lead temperature for soldering purpose	300					°C

## 2 Electrical characteristics

( $T_{CASE}=25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	600			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$ , $T_J = 125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$ ; $V_{DS} = 0$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 6.5\text{ A}$		0.260	0.285	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 50\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	1000	-	pF
$C_{oss}$	Output capacitance			60		pF
$C_{rss}$	Reverse transfer capacitance			3		pF
$C_{oss\text{ eq.}}^{(1)}$	Output equivalent capacitance	$V_{DS} = 0$ , to $480\text{ V}$ , $V_{GS} = 0$	-	225	-	pF
$R_g$	Intrinsic resistance	$f = 1\text{ MHz}$ open drain	-	3.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 13\text{ A}$ $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 18</a> )	-	35	-	nC
$Q_{gs}$	Gate-source charge			6		nC
$Q_{gd}$	Gate-drain charge			20		nC

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DS}$ .

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 13\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 17</a> )	-	20	-	ns
$t_r$	Rise time			22		ns
$t_{d(off)}$	Turn-off delay time			50		ns
$t_f$	Fall time			40		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		13	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		52	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 13\text{ A}$ , $V_{GS}=0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 13\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 19</a> )	-	300		ns
$Q_{rr}$	Reverse recovery charge		-	4.0		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	25		A
$t_{rr}$	Reverse recovery time	$V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ , $I_{SD} = 13\text{ A}$ $T_j = 150^\circ\text{C}$ (see <a href="#">Figure 19</a> )	-	360		ns
$Q_{rr}$	Reverse recovery charge		-	4.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	25		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D<sup>2</sup>PAK, I<sup>2</sup>PAK

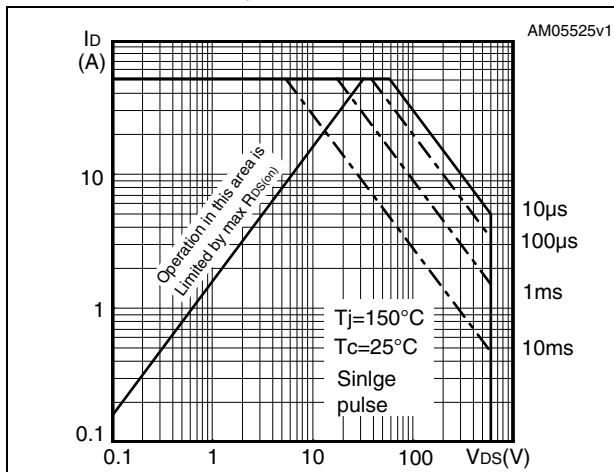


Figure 3. Thermal impedance for TO-220, D<sup>2</sup>PAK, I<sup>2</sup>PAK

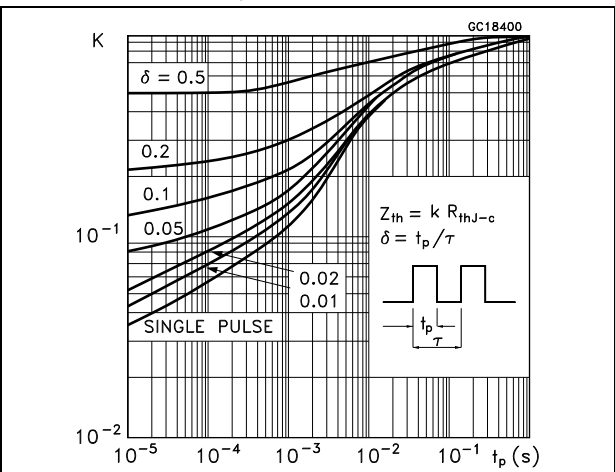


Figure 4. Safe operating area for TO-220FP

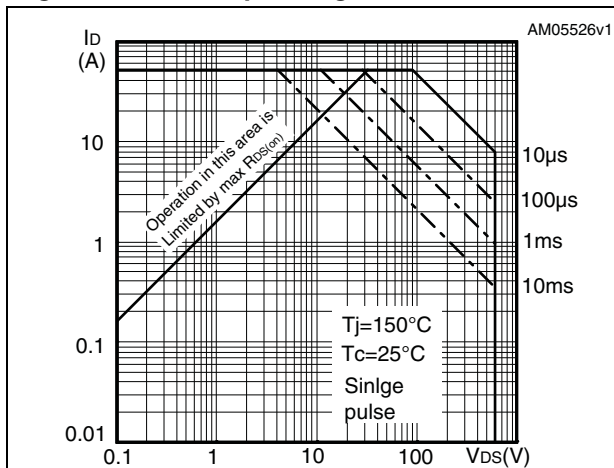


Figure 5. Thermal impedance for TO-220FP

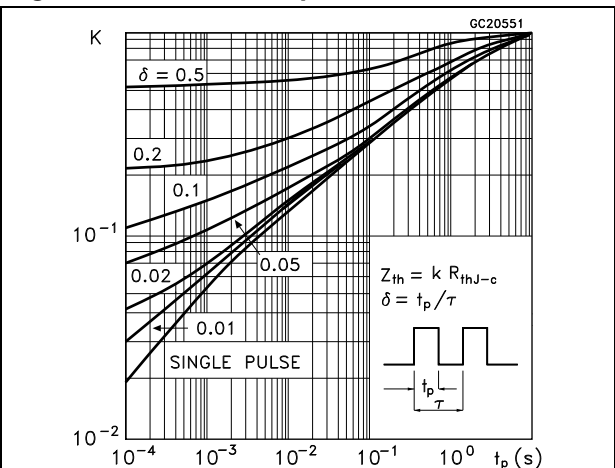


Figure 6. Safe operating area for TO-247

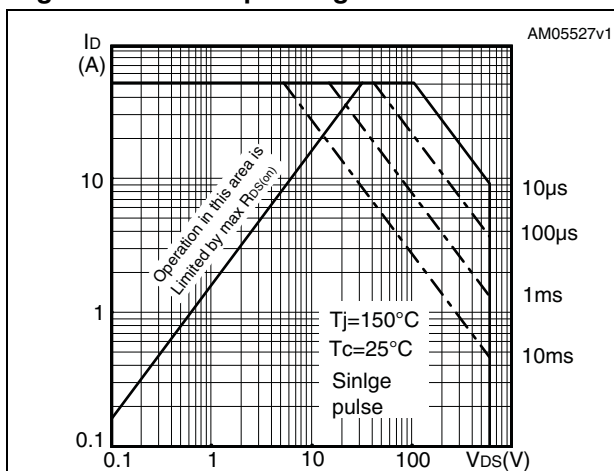


Figure 7. Thermal impedance for TO-247

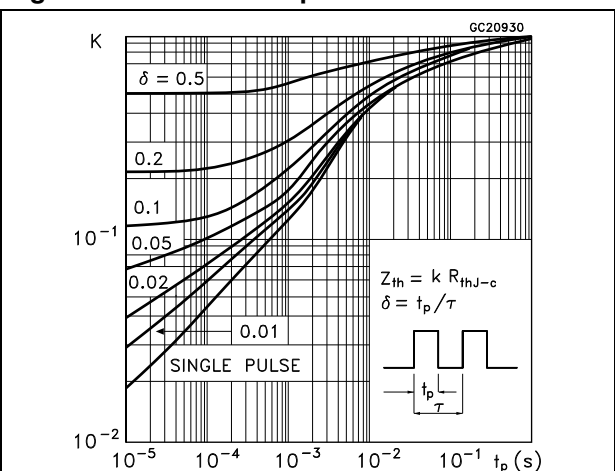


Figure 8. Output characteristics

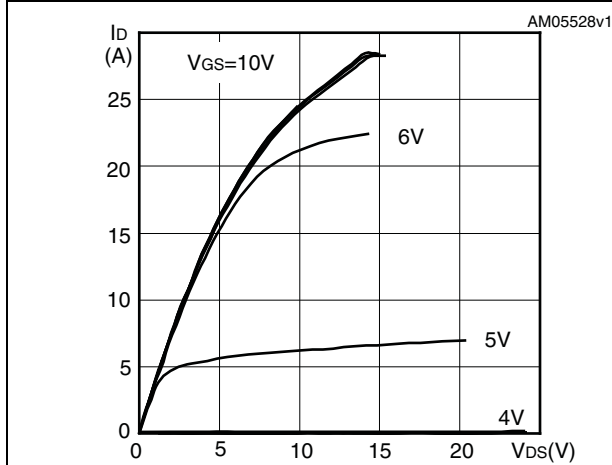


Figure 9. Transfer characteristics

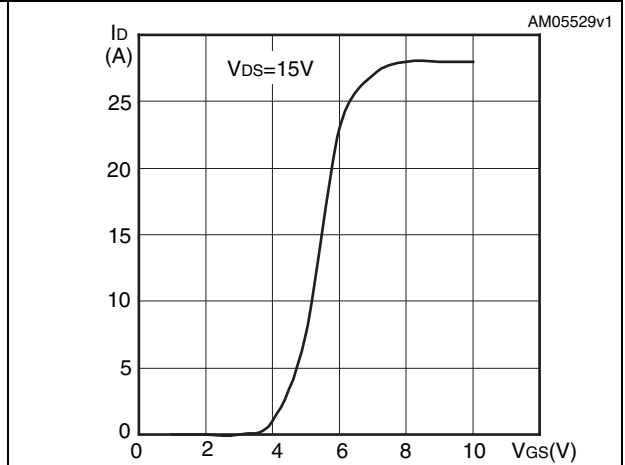


Figure 10. Static drain-source on resistance

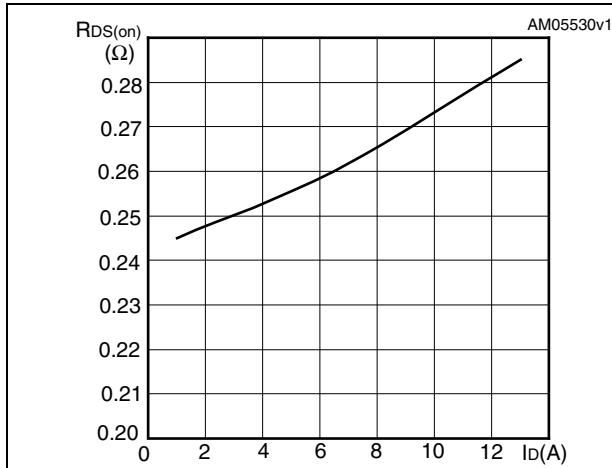


Figure 11. Gate charge vs gate-source voltage

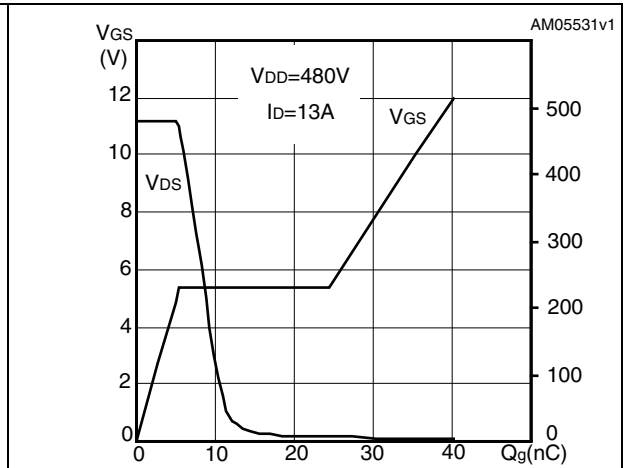


Figure 12. Capacitance variations

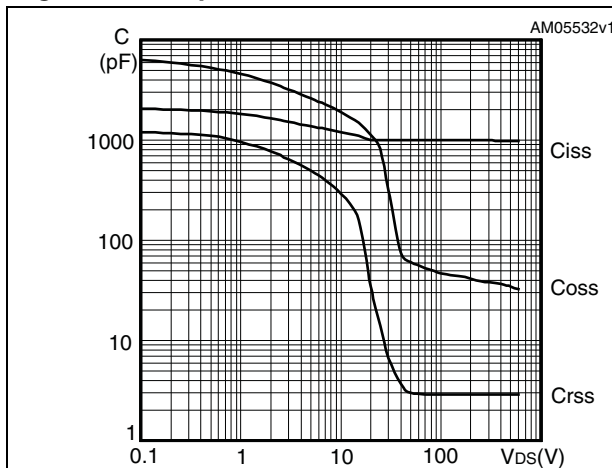
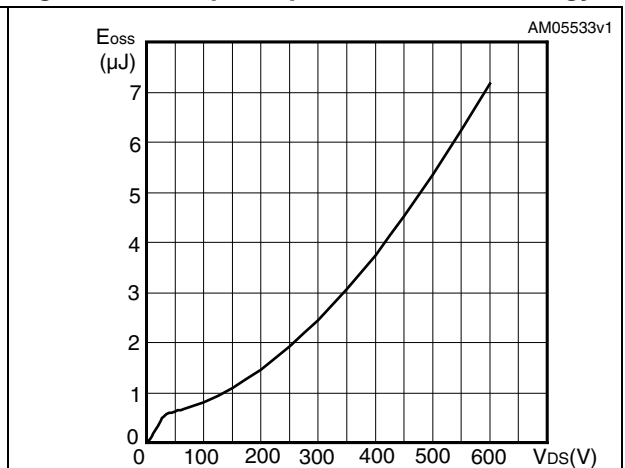
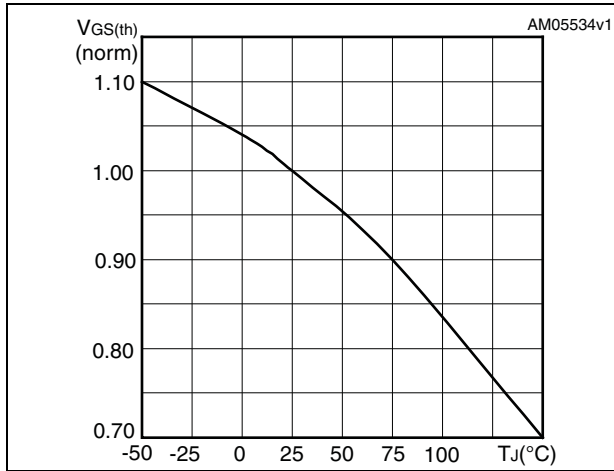


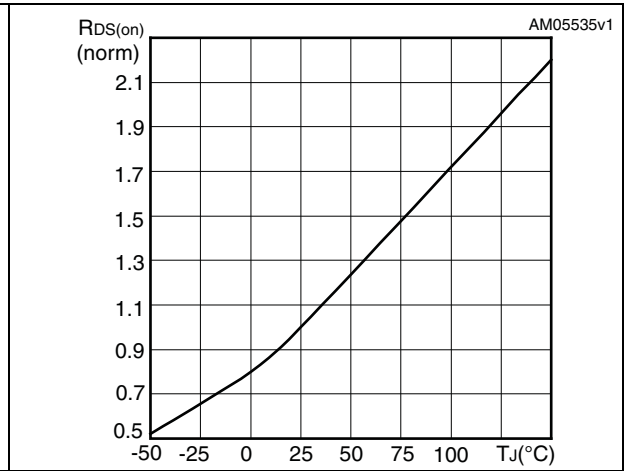
Figure 13. Output capacitance stored energy



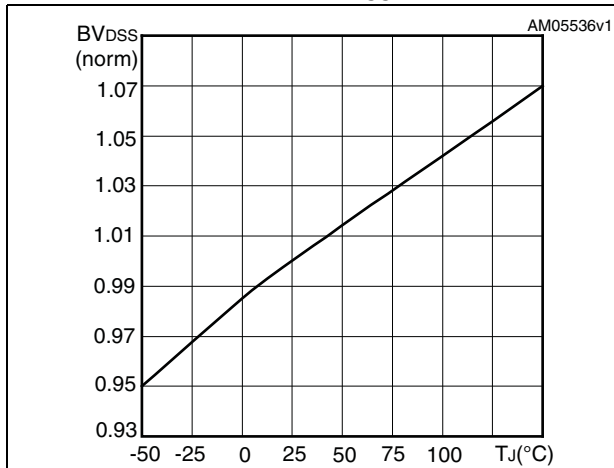
**Figure 14. Normalized gate threshold voltage vs temperature**



**Figure 15. Normalized on resistance vs temperature**



**Figure 16. Normalized B<sub>VDSS</sub> vs temperature**



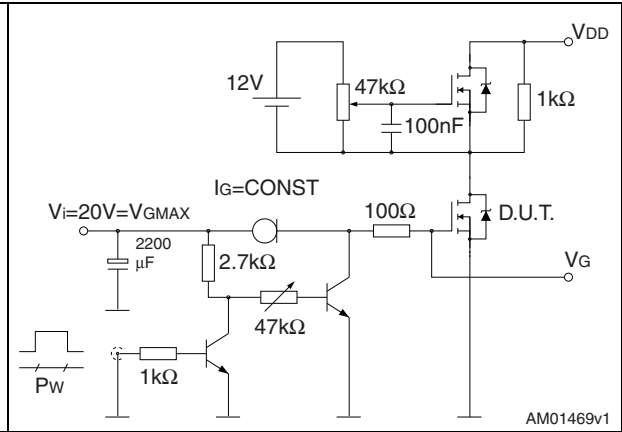


### 3 Test circuits

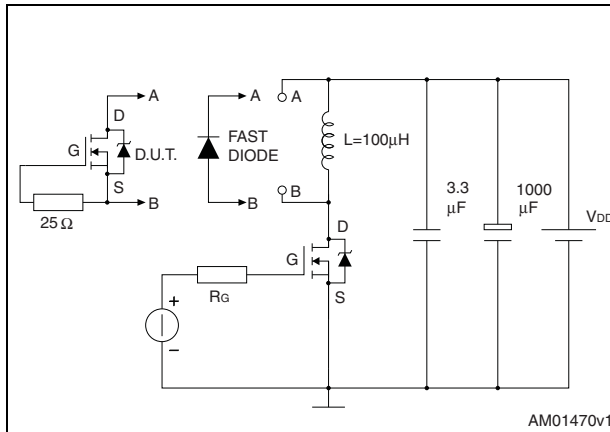
**Figure 17. Switching times test circuit for resistive load**



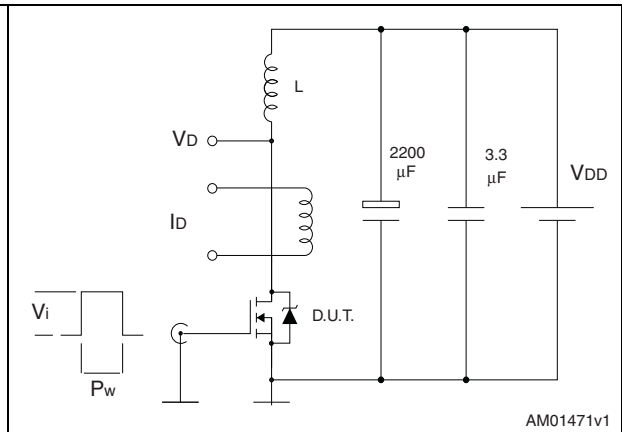
**Figure 18. Gate charge test circuit**



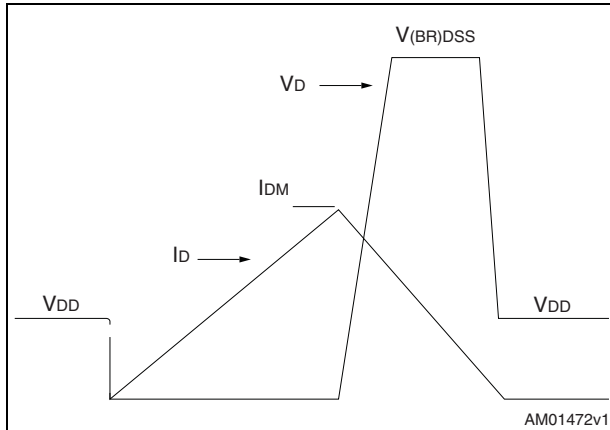
**Figure 19. Test circuit for inductive load switching and diode recovery times**



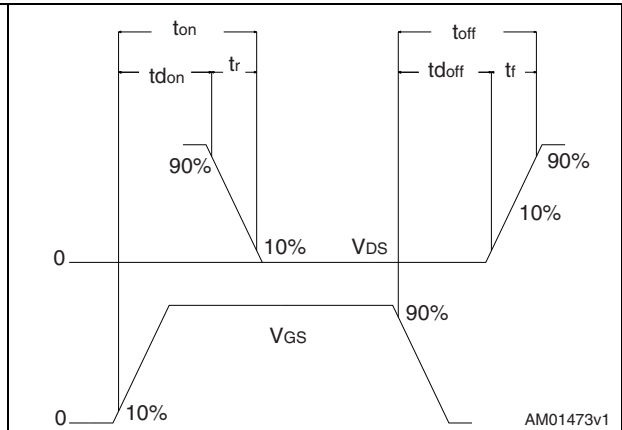
**Figure 20. Unclamped inductive load test circuit**



**Figure 21. Unclamped inductive waveform**



**Figure 22. Switching time waveform**



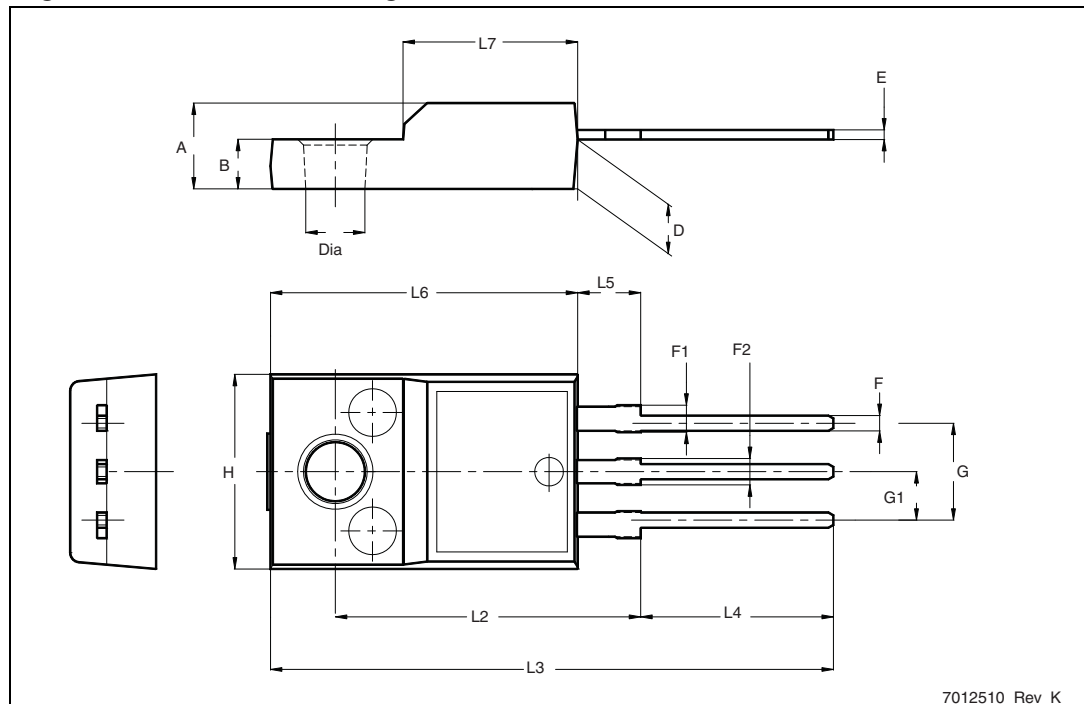
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 8. TO-220FP mechanical data

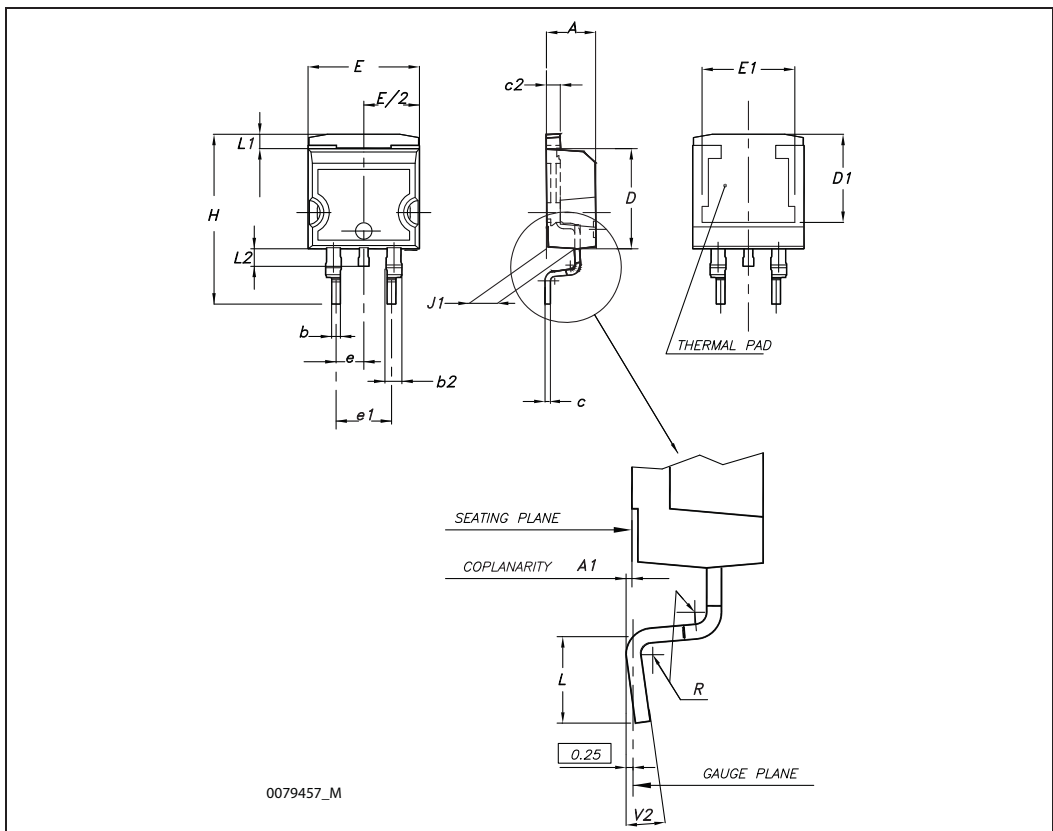
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 23. TO-220FP drawing mechanical data



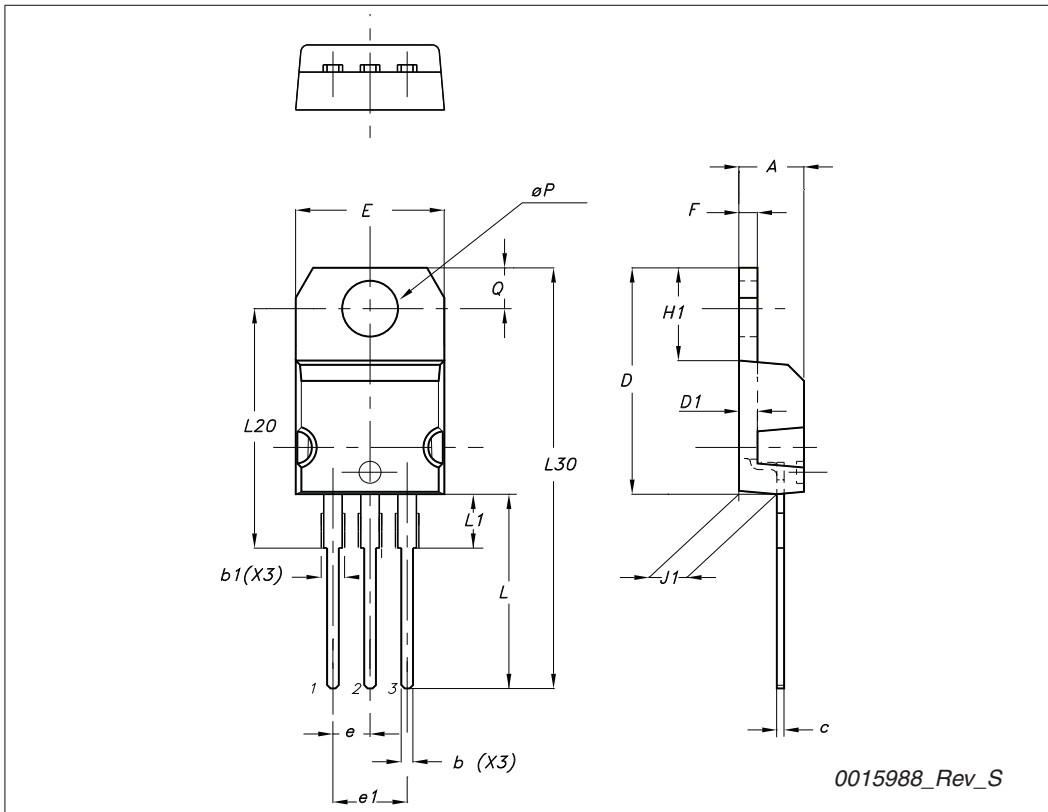
D<sup>2</sup>PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



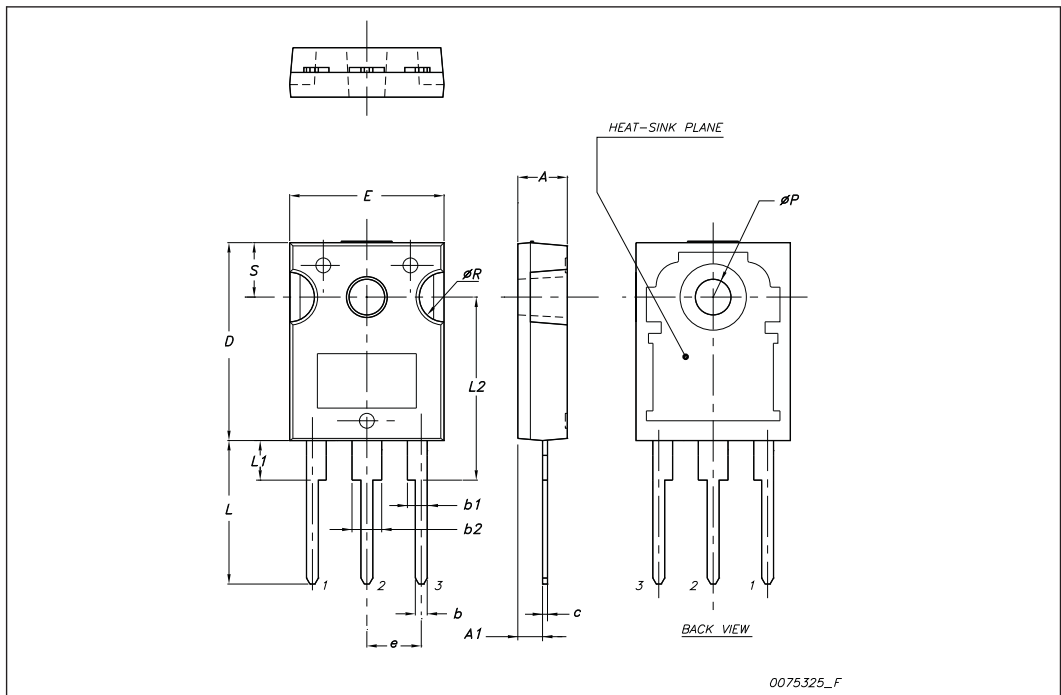
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



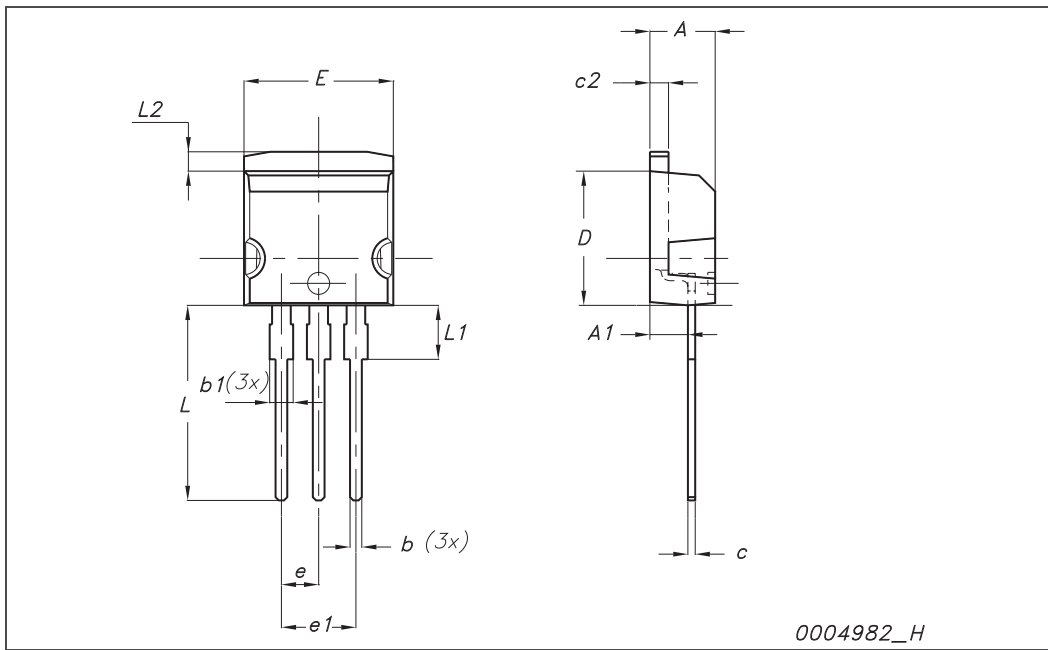
**TO-247 mechanical data**

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



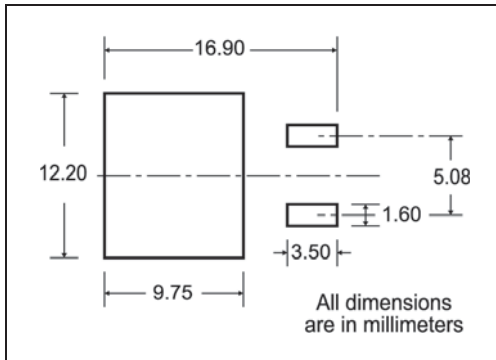
I<sup>2</sup>PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



# 5 Packaging mechanical data

D<sup>2</sup>PAK FOOTPRINT



TAPE AND REEL SHIPMENT

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000



## 6 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
15-Jun-2009	1	First release
11-Nov-2009	2	<ul style="list-style-type: none"><li>– Added <math>R_{DS(on)}</math> typical value</li><li>– Added new package, mechanical data: I<sup>2</sup>PAK</li><li>– Document status promoted from preliminary data to datasheet</li></ul>
06-Oct-2010	3	Inserted new value in <a href="#">Table 5</a> .

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